

INTEGRATED CIRCUIT HAVING INDEPENDENTLY FORMED
ARRAY AND PERIPHERAL ISOLATION DIELECTRICS

ABSTRACT OF THE DISCLOSURE

5 The invention comprises a method of forming an integrated circuit, the method comprising: (1) forming a first dielectric layer disposed outwardly from a semiconductor substrate; (2) forming a first intermediate structure outwardly from the a dielectric layer, the first intermediate structure comprising a floating gate layer disposed outwardly from the first dielectric layer, a second dielectric layer disposed outwardly from the floating gate layer, and a first polysilicon layer disposed outwardly from the second dielectric layer; (3) removing regions of the first intermediate structure to form at least one gate stack disposed outwardly from the first dielectric layer; and (4) forming at least one dielectric isolation region after the formation of the gate stacks, wherein the at least one dielectric isolation region is disposed between two gate stacks.

10

15

000220 5492960